

BACK-END

MOS-FET

IGBT

DIODE

SWITCHING TIME TEST SYSTEM スイッチングタイムテストシステム

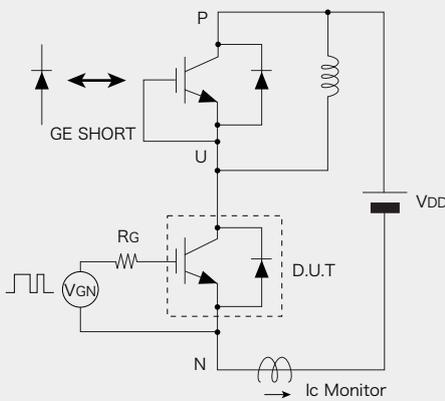
SWQRL1020Z

1000V
200A

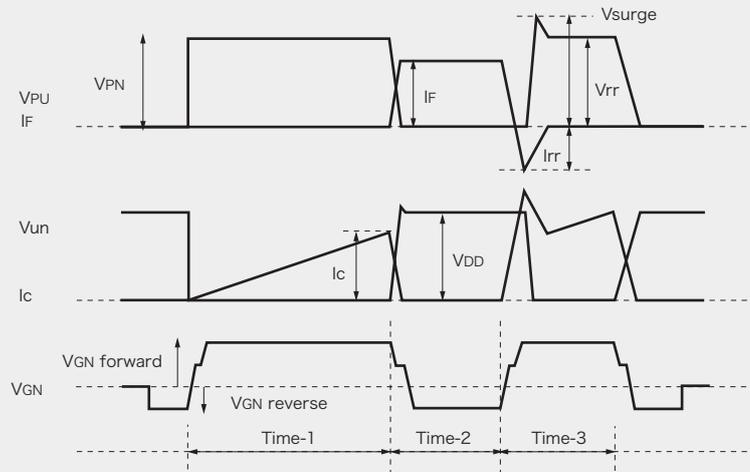
- SWQRL1020Z has been designed to be as compact as possible, with sufficient measurement space for workability. The construction corresponds to the measurement of the measuring section mainly 3-terminal products.
- SWQRL1020Z は作業性を重視した測定スペースを十分に確保し、できる限りコンパクトにまとめ上げた装置です。測定部は主に 3 端子品の測定に対応した構造となっています。



Fundamental Test Circuit (L-LOAD Switching)



Measurement Waveform (L-LOAD Switching)



MODEL	SWQRL1020Z	
TEST ITEMS		
R-LOAD/L-LOAD SWITCHING	Ic(I _D), td(on), tr, td(off), tf, e(on), e(off)	
di/dt	I _{rr} , trr, Q _{rr} , dif/dt, dir/dt, Vdsurge	
QG	Q _{gs} , Q _{gd} , Q _g , V _{th}	
SETTING RANGE		
MEASURABLE DEVICE	MOS-FET, IGBT, DIODE	
MEASUREMENT RANGE	000.0μs~9999μs	
VDD	20V~1000V	1V STEP
Id(Limit)	1.0A~200.0A	0.1A STEP
VGF/VGR	±00.00V~±30.00V	0.01V STEP
IG	±0.1mA~±10.0mA	0.1mA STEP
Time-1	000.0μs~999.9μs	0.1μs STEP
Time-2	000.0μs~999.9μs	0.1μs STEP
Time-3	00.0μs~99.9μs	0.1μs STEP
Time-4	000μs~9999μs	1μs STEP
RgF/RgR	0.0Ω~99.9Ω	0.1Ω STEP
BINNING		
OPEN/SHORT CHECK	VF1 > 5V...OPEN VKA < 8V...SHORT	
BIN INDICATION	ERROR, PASS, LIMIT-FAIL, OPEN, SHORT	
DIMENSIONS & WEIGHT		
MAIN UNIT	1070(W)×1050(D)×1860(H)…400kg	